

[METHOD FOR FORMING OPENING AND APPLICATION THEREOF]

Abstract of Disclosure

A method for forming an opening is described. A material layer, a patterned protective layer and a photoresist layer are sequentially formed on a substrate. A first exposure step is performed to form a line/space image on the photoresist layer with a first exposure dosage lower than that required for development. A second exposure step is then performed to define a region to be removed in the photoresist layer with a second exposure dosage, while the sum of the first and the second exposure dosages is equal to that required for development. A development step is conducted to remove the photoresist layer in the region to expose a portion of the patterned protective layer and a portion of the material layer. An etching process is then performed to form an opening in the material layer by using the photoresist layer and the patterned protective layer as a mask.

Figures